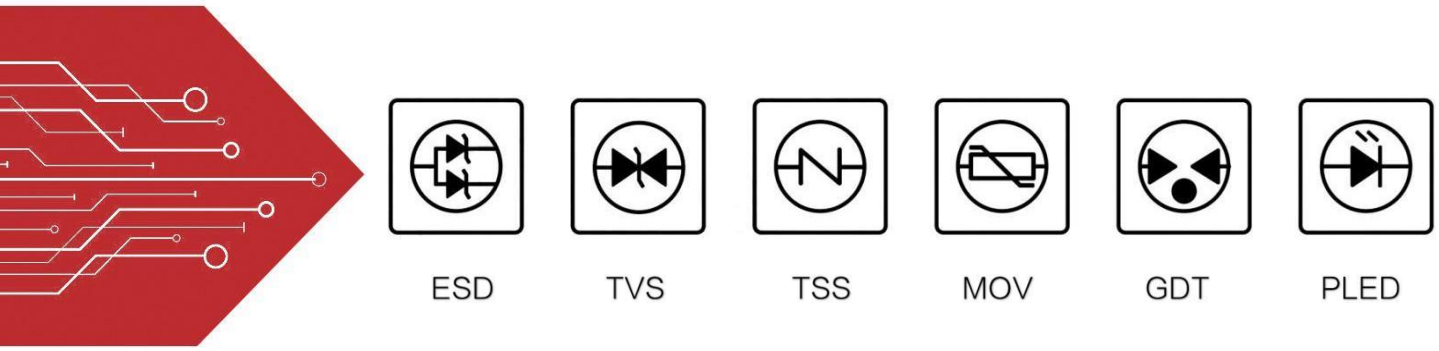
MSKSEMI
SEMICONDUCTOR

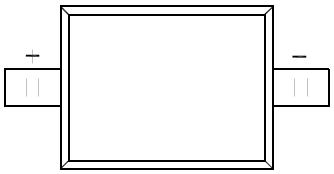


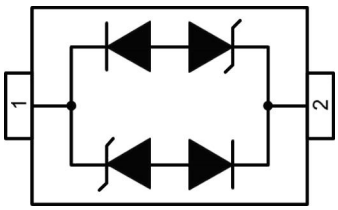
Product data sheet

www.msksemi.com

Features

- 350W peak pulse power (8/20μs)
- Ultra low capacitance ： 1.0pF typical
- Ultra low leakage：nA level
- Low Operating：3.3V,5V,8V,12V,15V,24V
- Low clamping voltage
- Protects one power line or data line
- Complies with following standards:
  – IEC 61000-4-2 (ESD) immunity test
  Air discharge: ±30kV
  Contact discharge: ±30kV
  – IEC61000-4-4 (EFT) 40A (5/50ns)
- RoHS Compliant





Circuit and Pin Schematic

SOD-323

Mechanical Characteristics

- Package: SOD-323
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- USB Ports
- Smart Phones
- Wireless Systems
- Ethernet 10/100/1000 Base T

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	V_{ESD}	±30 ±30	kV
Operating Temperature Range	T_J	−40 to +85	°C
Storage Temperature Range	Tstg	−55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

GBLC03C-MS						
Parameter	**Symbol**	**Min**	**Typ**	**Max**	**Unit**	**Test Condition**
Reverse Working Voltage	V_{RWM}			3.3	V	
Breakdown Voltage	V_{BR}	4			V	I_T = 1mA
Reverse Leakage Current	I_R		1	100	nA	V_{RWM} = 3.3V
Clamping Voltage	V_C			7	V	I_{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	V_C			16	V	I_{PP} = 20A (8 x 20μs pulse)
Peak Pulse Current	I_{PP}			20	A	tp=8/20μs
Junction Capacitance	C_J		1		pF	VR = 0V, f = 1MHz

GBLC05C-MS						
Parameter	**Symbol**	**Min**	**Typ**	**Max**	**Unit**	**Test Condition**
Reverse Working Voltage	V_{RWM}			5	V	
Breakdown Voltage	V_{BR}	6			V	I_T = 1mA
Reverse Leakage Current	I_R		1	100	nA	V_{RWM} = 5V
Clamping Voltage	V_C			10	V	I_{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	V_C			18	V	I_{PP} = 18A (8 x 20μs pulse)
Peak Pulse Current	I_{PP}			18	A	tp=8/20μs
Junction Capacitance	C_J		1		pF	VR = 0V, f = 1MHz

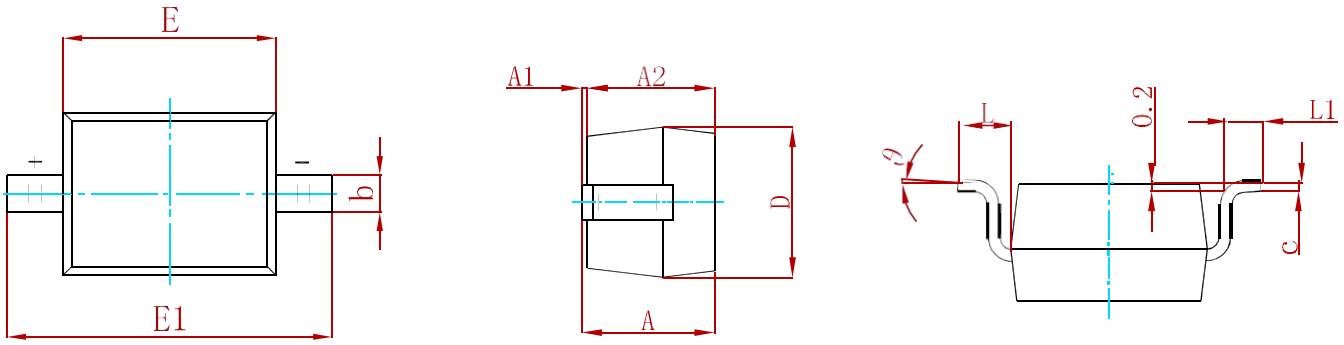
GBLC08C-MS						
Parameter	**Symbol**	**Min**	**Typ**	**Max**	**Unit**	**Test Condition**
Reverse Working Voltage	V_{RWM}			8	V	
Breakdown Voltage	V_{BR}	8.5			V	I_T = 1mA
Reverse Leakage Current	I_R		1	100	nA	V_{RWM} = 8V
Clamping Voltage	V_C			14	V	I_{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	V_C			19	V	I_{PP} = 13A (8 x 20μs pulse)
Peak Pulse Current	I_{PP}			13	A	tp=8/20μs
Junction Capacitance	C_J		1		pF	VR = 0V, f = 1MHz

GBLC12C-MS						
Parameter	**Symbol**	**Min**	**Typ**	**Max**	**Unit**	**Test Condition**
Reverse Working Voltage	V_{RWM}			12	V	
Breakdown Voltage	V_{BR}	13.3			V	I_T = 1mA
Reverse Leakage Current	I_R		1	100	nA	V_{RWM} = 12V
Clamping Voltage	V_C			19	V	I_{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	V_C			25	V	I_{PP} = 10A (8 x 20μs pulse)
Peak Pulse Current	I_{PP}			10	A	tp=8/20μs
Junction Capacitance	C_J		1		pF	VR = 0V, f = 1MHz

GBLC15C-MS						
Parameter	**Symbol**	**Min**	**Typ**	**Max**	**Unit**	**Test Condition**
Reverse Working Voltage	V_{RWM}			15	V	
Breakdown Voltage	V_{BR}	16.7			V	I_T = 1mA
Reverse Leakage Current	I_R		1	100	nA	V_{RWM} = 15V
Clamping Voltage	V_C			20	V	I_{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	V_C			31	V	I_{PP} = 8A (8 x 20μs pulse)
Peak Pulse Current	I_{PP}			8	A	tp=8/20μs
Junction Capacitance	C_J		1		pF	VR = 0V, f = 1MHz

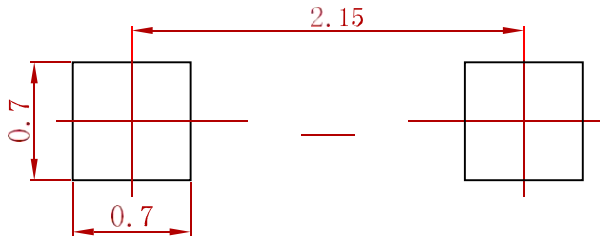
GBLC24C-MS						
Parameter	**Symbol**	**Min**	**Typ**	**Max**	**Unit**	**Test Condition**
Reverse Working Voltage	V_{RWM}			24	V	
Breakdown Voltage	V_{BR}	26.7			V	I_T = 1mA
Reverse Leakage Current	I_R		1	100	nA	V_{RWM} = 24V
Clamping Voltage	V_C			40	V	I_{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	V_C			71	V	I_{PP} = 3.5A (8 x 20μs pulse)
Peak Pulse Current	I_{PP}			3.5	A	tp=8/20μs
Junction Capacitance	C_J		1		pF	VR = 0V, f = 1MHz

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A		1.000		0.039
A1	0.000	0.100	0.000	0.004
A2	0.800	0.900	0.031	0.035
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.550	2.750	0.100	0.108
L	0.475 REF.		0.019 REF.	
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
GBLCXXC-MS	SOD-323	3000

Attention

■ Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

■ MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specificationsof any andall MSKSEMI Semiconductor products described orcontained herein.

■ Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer'sproducts orequipment.

■ MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possiblethat these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuitsfor safedesign, redundant design, and structural design.

■ In the event that any or all MSKSEMI Semiconductor products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

■ Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringementsof intellectual property rights or other rightsof third parties.

■ Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.

单击下面可查看定价，库存，交付和生命周期等信息

>>MSKSEMI(美森科)